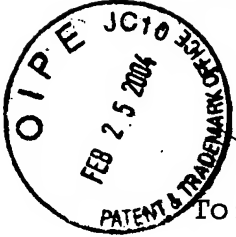


TSMC-01-714C



February 18, 2004

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Aavenue  
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/755,498 01/12/04

Bor-Wen Chan et al.

A METHOD OF FORMING A STACKED  
CAPACITOR STRUCTURE WITH INCREASED  
SURFACE AREA FOR A DRAM DEVICE

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on February 23, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 2/23/04

U.S. Patent 6,025,225 to Forbes et al., "Circuits with a Trench Capacitor Having Micro-Roughened Semiconductor Surfaces and Methods for Forming the Same," discloses a trench cap process with roughened sides.

U.S. Patent 5,923,989 to Lin et al., "Method of Fabricating Rugged Capacitor of High Density DRAMs," reveals a stacked Cap process with Hemispherical grains (HSG).

U.S. Patent 5,691,221 to Jun, "Method for Manufacturing Semiconductor Memory Device Having a Stacked Capacitor," discloses a fin capacitor.

U.S. Patent 5,670,405 to Tseng, "Method of Making a Tooth Shaped Capacitor Using Ion Implantation," discloses a method of manufacturing a capacitor for use in semiconductor memories.

U.S. Patent 5,801,089 to Kenney, "Method of Forming Stacked Devices," discloses chips having subsurface structures within or adjacent to a horizontal trench in bulk single crystal semiconductors.

TSMC-01-714C

U.S. Patent 6,057,205 to Wu, "Method to Form a Ragged Poly-Si Structure for High Density DRAM Cells," discloses a method for fabricating a capacitor on a semiconductor device.

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman", with a long horizontal flourish extending to the right.

Stephen B. Ackerman, Reg. #37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

TSMC-01-714C

Application Number

10/755,498

Applicant

Bor-Wen Chan et al.

Filing Date

01/12/04

Group Art Unit

## U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
	6025225	2/15/00	Forbes et al.	438	243	1/22/98
	5923989	7/13/99	Lin et al.	438	398	5/20/98
	5691221	11/25/97	Jun	437	52	8/15/96
	5670405	9/23/97	Tseng	437	52	1/30/97
	6057205	5/2/00	Wu	438	398	1/28/98
	5801089	9/1/98	Kenney	438	589	6/7/95

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

